

gas holes 3. Designated at numeral 10 in Fig. 2 typically illustrates the entrance of the plasma into the backside of the gas-introducing plate 4. When the plasma enters therein, the state of discharge of the plasma on the wafer side becomes unstable. As a result, an etching characteristic is deteriorated and the wafer 8 is unusually processed.

In the Abstract of the Disclosure

At page 19, after the heading "Abstract of the Disclosure," please delete the paragraphs that begin "A problem arose..." and "In order to...". Please replace these paragraphs with the following paragraph:

A pressure detector is provided inside an upper electrode of a parallel plate type dry-etching apparatus. Upon reaching a particular pressure at the detector, the etching apparatus is deactivated. This deactivation may be used to replace an ineffective gas introducing plate.

In the Drawings

Please amend Fig. 2 per the proposed handwritten changes in red ink.

In the Claims

Please amend the claims as follows:

3. **(Twice Amended)** An apparatus for manufacturing a semiconductor device, comprising:

an upper electrode that supplies gas to a parallel-plate dry etching apparatus; and